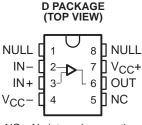
- Very High Speed
 - -270 MHz Bandwidth (Gain = 1, -3 dB)
 - 400 V/μsec Slew Rate
 - 40-ns Settling Time (0.1%)
- High Output Drive, I_O = 100 mA
- Excellent Video Performance
 - 60 MHz Bandwidth (0.1 dB, G = 1)
 - 0.04% Differential Gain
 - 0.15° Differential Phase
- Very Low Distortion
 - THD = -72 dBc at f = 1 MHz
- Wide Range of Power Supplies
 V_{CC} = ± 2.5 V to ± 15 V,
 I_{CC} = 7.5 mA
- Evaluation Module Available

description

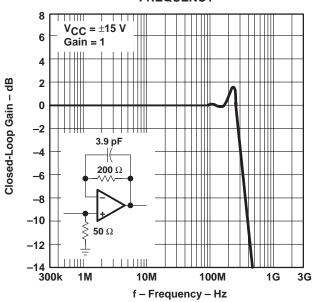
The THS4001 is a very high-performance, voltage-feedback operational amplifier especially suited for a wide range of video applications. The device is specified to operate over a wide range of supply voltages from \pm 15 V to \pm 2.5 V. With a bandwidth of 270 MHz, a slew rate of over 400 V/ μ s, and settling times of less than 30 ns, the THS4001 offers the unique combination of high performance in an easy to use voltage feedback configuration over a wide range of power supply voltages.

The THS4001 is stable at all gains for both inverting and noninverting configurations. It has a high output drive capability of 100 mA and draws



NC – No internal connection

CLOSED-LOOP GAIN vs FREQUENCY



only 7.5 mA of quiescent current. Excellent professional video results can be obtained with the differential gain/phase performance of $0.04\%/0.15^{\circ}$ and 0.1 dB gain flatness to 60 MHz. For applications requiring low distortion, the THS4001 is ideally suited with total harmonic distortion of -72 dBc at f = 1 MHz.

HIGH-SPEED AMPLIFIER FAMILY

| DEVICE | AR | CH. | SUPPLY VOLTAGE | | BW SR (V/μs) | | THD f = 1 MHz | t _S 0.1% | DIFF. GAIN | DIFF. PHASE | V _{n_} | |
|------------|-----|-----|-------------------|------|--------------|---------|------------------|------------------------|---------------|----------------|-----------------|----------|
| | VFB | CFB | 5 V | ±5 V | ±15 V | (WITIZ) | (ν/μs) | (dB) | (ns) | GAIN | FHASE | (nV/√Hz) |
| THS3001 | | • | | • | • | 420 | 6500 | -96 | 40 | 0.01% | 0.02° | 1.6 |
| THS4001 | • | | • | • | • | 270 | 400 | -72 | 40 | 0.04% | 0.15° | 12.5 |
| THS4031/32 | • | | | • | • | 100 | 100 | -72 | 60 | 0.02% | 0.03° | 1.6 |
| THS4061/62 | • | | | • | • | 180 | 400 | -72 | 40 | 0.02% | 0.02° | 14.5 |



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

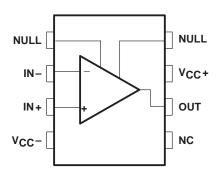


AVAILABLE OPTIONS

| | PACKAGED DEVICES | | | | | |
|---------------|-----------------------------------|----------------------|--|--|--|--|
| TA | SMALL OUTLINE [†] (D) | EVALUATION MODULE | | | | |
| 0°C to 70°C | THS4001CD | THS4001EVM | | | | |
| -40°C to 85°C | THS4001ID | _ | | | | |

[†]The D packages are available taped and reeled. Add an R suffix to the device type (i.e., THS4001CDR).

symbol



absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

| Supply voltage, V _{CC} to V _{CC+} | 33 V |
|--|------------------|
| Input voltage, V _I | ±V _{CC} |
| Output current, I _O | |
| Differential input voltage, V _{ID} | |
| Continuous total power dissipation | |
| Operating free air temperature, T _A :C suffix | 0°C to 70 °C |
| I suffix | –40°C to 85 °C |
| Storage temperature, T _{stq} | 65°C to 150 °C |
| Lead temperature 1,6 mm (1/16 lnch) from case for 10 seconds | 300°C |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

| PACKAGE | $\begin{aligned} & \textbf{T}_{\pmb{A}} \leq \textbf{25}^{\circ}\textbf{C} \\ & \textbf{POWER RATING} \end{aligned}$ | DERATING FACTOR ABOVE T _A = 25°C | T _A = 70°C POWER RATING | T _A = 85°C POWER RATING |
|---------|--|--|---------------------------------------|---------------------------------------|
| D | 740 mW | 6 mW/°C | 475 mW | 385 mW |



CAUTION: The THS4001 provides ESD protection circuitry. However, permanent damage can still occur if this device is subjected to high-energy electrostatic discharges. Proper ESD precautions are recommended to avoid any performance degradation or loss of functionality



recommended operating conditions

| | | MIN | TYP | MAX | UNIT |
|--|---------------|------|-----|-----|------|
| Supply voltage Vale | Dual supply | ±2.5 | | ±16 | V |
| Supply voltage, V _{CC} | Single supply | 5 | | 32 | V |
| Quiescent current les | ±15 V | | 7.8 | 9.5 | m ^ |
| Quiescent current, I _{CC} | ±5 V, ±2.5 V | | 6.7 | 8 | mA |
| Operating free circlemporature T | C suffix | 0 | | 70 | °C |
| Operating free-air temperature, T _A | I suffix | -40 | | 85 | -0 |

electrical characteristics, V_{CC} = ± 15 V, R_L = 150 Ω , T_A = 25°C (unless otherwise noted)

| | PARAMETER | TEST CO | TEST CONDITIONS | | | TYP | MAX | UNIT |
|-----------------|---------------------------------|--|---|-----------------------------|-----------|-----------|-----|--------|
| | D''' (1) | | | V_{CC} ±15 V | | 0.04% | | |
| | Differential gain error | Gain = 2, | R _L = 150 Ω, | ±5 V | | 0.01% | | |
| | Differential above areas | f = 3.58 MHz | | ±15 V | | 0.15° | | |
| | Differential phase error | | | ±5 V | | 0.08° | | |
| \/10 | Input offset voltage | T _A = 25°C | | ±15 V, | | 2 | 8 | m\/ |
| VIO | input onset voltage | T _A = full range | | ±5 V | | | 10 | mV |
| I _{IB} | Input bias current | T _A = 25°C | | ±15 V, | | 2.6 | 5 | μА |
| אוי | input bias current | T _A = full range | | ±5 V | | | 6 | μΑ |
| loo | Input offeet current | T _A = 25°C | | ±15 V, | | 35 | 200 | nA |
| los | Input offset current | T _A = full range | | ±5 V | | | 500 | |
| | | V _O = ±10 V, | T _A = 25°C | 145.1/ | 5 | 10 | | |
| | Open leen gein | $R_L = 1 k\Omega$ | T _A = full range | ±15 V | 3 | | | \//m\/ |
| | Open-loop gain | $V_0 = \pm 2.5 V$, | T _A = 25°C | 1.F.V | 3 | 6 | | V/mV |
| | | $R_L = 500 \Omega$ | T _A = full range | ±5 V | 2 | | | |
| CMDD | Common mode valuation vation | \/ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | T _A = 25°C | 145 \/ | 85 | 100 | | dB |
| CMRR | Common-mode rejection ratio | $V(CM) = \pm 12 V$ | $(CM) = \pm 12 \text{ V}$ $T_A = \text{full range}$ | ±15 V | 75 | | | |
| DCDD | Device comply rejection ratio | T _A = 25°C | ±15 V, | 75 | 85 | | 40 | |
| PSRR | Power supply rejection ratio | T _A = full range | | ±5 V | 70 | | | dB |
| | | | | | 13.5 | 14.8 | | · V |
| | | | | ±15 V | to -13 | to –14 | | |
| VICR | Common-mode input voltage range | | | | 3.6 | 4.4 | | |
| | | | | ±5 V | to | to | | |
| | | | | | -2.7 | -3.6 | | |
| | | | | ±15 V | ±13 | ±13.5 | | |
| Vo | Output voltage swing | $R_L = 500 \Omega$ | | ±5 V | ±3.3 | ±3.8 | | V |
| | | | | ±2.5 V | ±0.8 | ±1.3 | | |
| | | | | ±15 V | 50 | 100 | | |
| lO | Output current | | | ±5 V | 50 | 100 | | mA |
| | | | | ±2.5 V | 50 | 100 | | |
| THD | Total harmonic distortion | $V_I = 1 V_{(PP)}$ | f = 1 MHz | ±15 V | | -72 | | dBc |
| R _I | Input resistance | | | | | 10 | | МΩ |
| Cl | Input capacitance | | | | | 1.5 | | pF |
| RO | Output resistance | Open loop | | | | 10 | | Ω |

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operating characteristics, $V_{CC} = \pm 15 \text{ V}$, $R_L = 150 \Omega$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

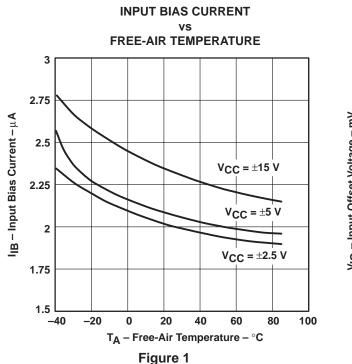
| | PARAMETER | TEST COND | ITIONS | VCC | MIN | TYP | MAX | UNIT |
|----------------|--------------------------------|--|--|----------------|-----|------|-----|--------------------|
| | | | | ±15 V | | 400 | | |
| | Slew rate | Gain = -1 | | ±5 V | | 400 | | V/μs |
| | | | | ±2.5 V | | 350 | | |
| | Settling time to 0.1% | 10 V step (0 to 10 V), | Gain = -1 | ±15 V | | 40 | | ns |
| | Setting time to 0.1 /6 | -2.5 V to 2.5 V step, | Gain = -1 | ±5 V | | 30 | | 115 |
| | | | | ±15 V | | 270 | | |
| | | Gain = +1, $R_f = 150 \Omega$ | (0 to 10 V), $Gain = -1$ 2.5 V step, $Gain = -1$, $R_L = 150 \Omega$, Ω | ±5 V | | 220 | | MHz |
| | -3 dB Bandwidth | 114 - 100 22 | | ±2.5 V | | 180 | | |
| | -3 db Baildwidtii | Gain = -1 , R _f = 150 Ω | $R_L = 150 \Omega$, | ±15 V | | 80 | | MHz |
| | | | | ±5 V | | 75 | | |
| | | 111 - 100 22 | | ±2.5 V | | 70 | | |
| | | | | ±15 V | | 60 | | |
| | Bandwidth for 0.1 dB flatness | Gain = +1 | | ±5 V | | 50 | | MHz |
| | | | | ±2.5 V | | 40 | | |
| v _n | Equivalent input noise voltage | f = 10 kHz | | ±15 V, ±5 V | | 12.5 | · | nV/√ Hz |
| In | Equivalent input noise current | f = 10 kHz | | ±15 V, ±5 V | | 1.5 | | pA/√ Hz |

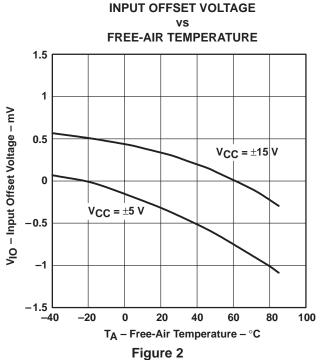
TYPICAL CHARACTERISTICS

Table of Graphs

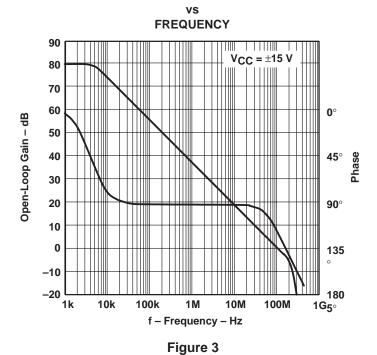
| | | | FIGURE |
|-----------------|------------------------------|-------------------------|--------|
| I _{IB} | Input bias current | vs Free-air temperature | 1 |
| VIO | Input offset voltage | vs Free-air temperature | 2 |
| | Open-loop gain | vs Frequency | 3 |
| | Phase | vs Frequency | 3 |
| | Differential gain | vs DC voltage | 4, 5 |
| | Differential phase | vs DC voltage | 4, 5 |
| | Closed-loop gain | vs Frequency | 6, 7 |
| CMRR | Common-mode rejection ratio | vs Frequency | 8 |
| DCDD | Danier aurah, miastian astia | vs Frequency | 9 |
| PSRR | Power-supply rejection ratio | vs Free-air temperature | 10 |
| \/ | Output valta as suria a | vs Supply voltage | 11 |
| VO(PP) | Output voltage swing | vs Load resistance | 12 |
| | Bandwidth (-3 dB) | vs Feedback resistance | 13, 14 |
| 1 | Committee | vs Supply voltage | 15 |
| ICC | Supply current | vs Free-air temperature | 16 |
| Env | Noise spectral density | vs Frequency | 17 |
| THD | Total harmonic distortion | vs Frequency | 18 |







OPEN-LOOP GAIN AND PHASE





DIFFERENTIAL GAIN AND DIFFERENTIAL PHASE

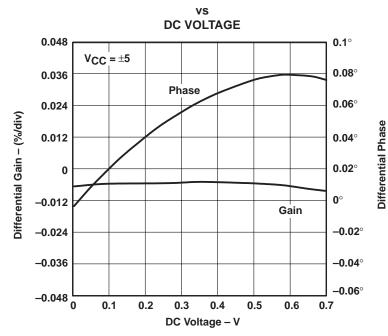


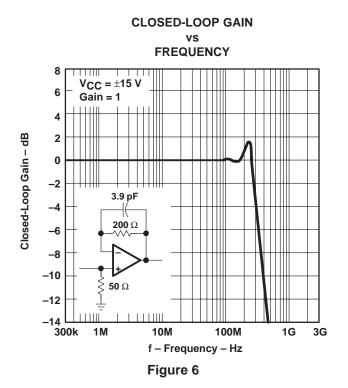
Figure 4

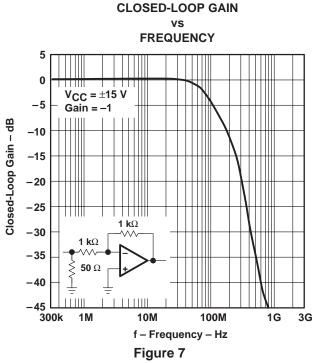
DIFFERENTIAL GAIN AND DIFFERENTIAL PHASE

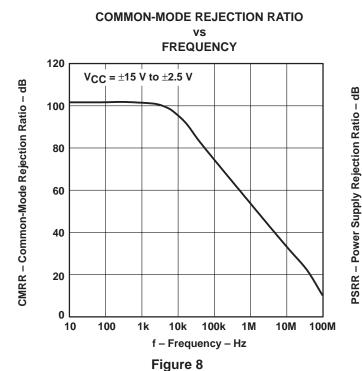
vs **DC VOLTAGE** 0.048 0.12° Phase $V_{CC} = \pm 15$ 0.1° 0.036 0.08° 0.024 Differential Gain – (%/div) 0.06° Differential Phase 0.012 Gain 0.04° 0 -0.012 $\textbf{0.02}^{\circ}$ **0**° -0.024-0.036 **-0.02**° **-0.04**° -0.048-0.06 L -0.06° 0.1 0.2 0.3 0.4 0.5 0.6 0.7 DC Voltage - V

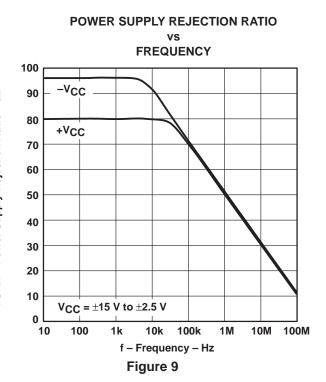
Figure 5

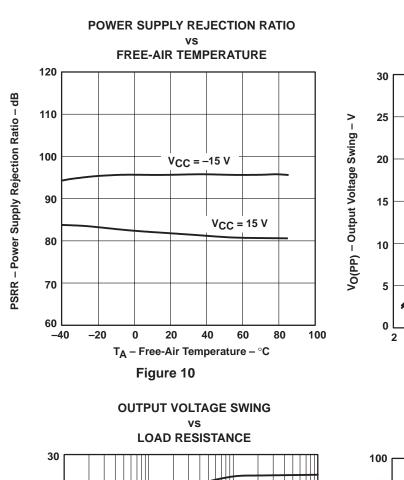


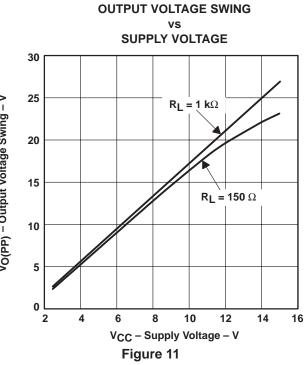


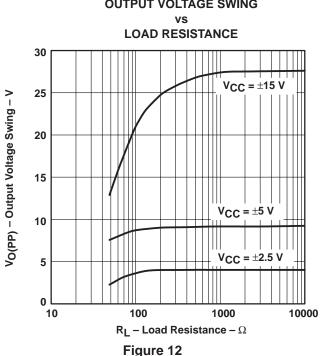


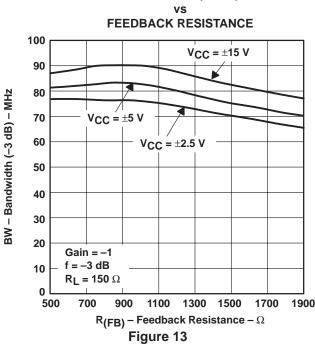




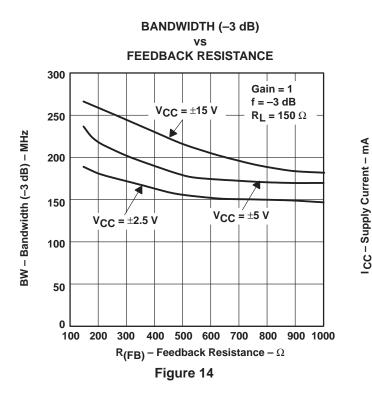


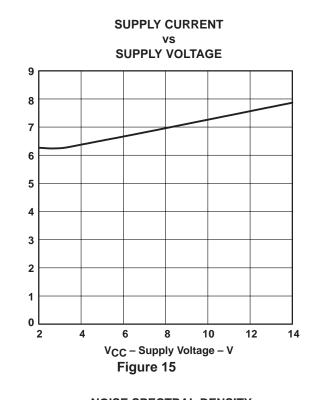


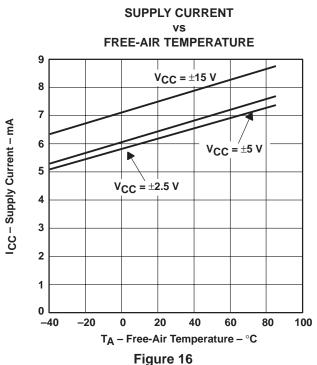


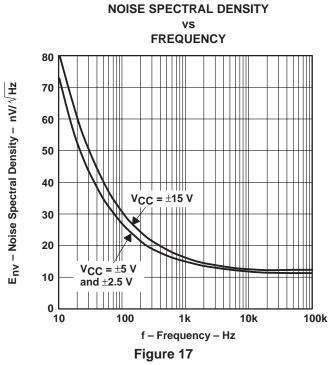


BANDWIDTH (-3 dB)

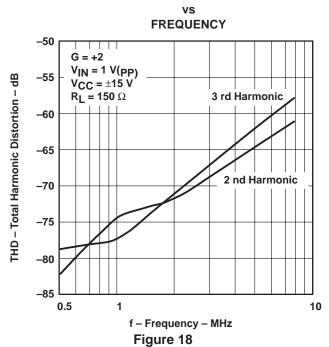








TOTAL HARMONIC DISTORTION



theory of operation

The THS4001 is a high speed, operational amplifier configured in a voltage feedback architecture. It is built using a 30-V, dielectrically isolated, complementary bipolar process with NPN and PNP transistors possessing f_{TS} of several GHz. This results in an exceptionally high performance amplifier that has a wide bandwidth, high slew rate, fast settling time, and low distortion. A simplified schematic is shown in Figure 19.

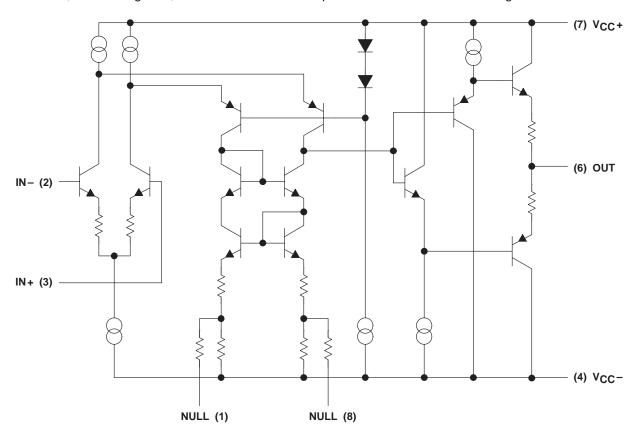


Figure 19. THS4001 Simplified Schematic

offset nulling

The THS4001 has very low input offset voltage for a high-speed amplifier. However, if additional correction is required, an offset nulling function has been provided. By placing a potentiometer between terminals 1 and 8 of the device and tying the wiper to the negative supply, the input offset can be adjusted. This is shown in Figure 20.

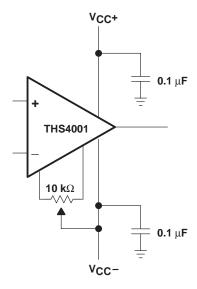


Figure 20. Offset Nulling Schematic

optimizing unity gain response

Internal frequency compensation of the THS4001 was selected to provide very wideband performance yet still maintain stability when operated in a noninverting unity gain configuration. When amplifiers are compensated in this manner there is usually peaking in the closed loop response and some ringing in the step response for very fast input edges, depending upon the application. This is because a minimum phase margin is maintained for the G=+1 configuration. For optimum settling time and minimum ringing, a feedback resistor of $200\,\Omega$ should be used as shown in Figure 21. Additional capacitance can also be used in parallel with the feedback resistance if even finer optimization is required.

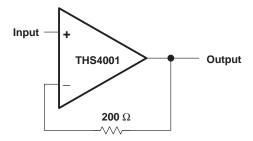


Figure 21. Noninverting, Unity Gain Schematic



driving a capacitive load

Driving capacitive loads with high performance amplifiers is not a problem as long as certain precautions are taken. The first is to realize that the THS4001 has been internally compensated to maximize its bandwidth and slew rate performance. When the amplifier is compensated in this manner, capacitive loading directly on the output will decrease the device's phase margin leading to high frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, it is recommended that a resistor be placed in series with the output of the amplifier, as shown in Figure 22. A minimum value of 20 Ω should work well for most applications. For example, in 75- Ω transmission systems, setting the series resistor value to 75 Ω both isolates any capacitance loading and provides the proper line impedance matching at the source end.

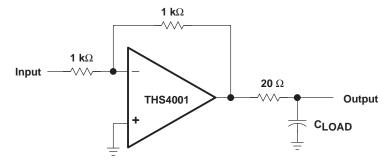


Figure 22. Driving a Capacitive Load

circuit layout considerations

In order to achieve the levels of high frequency performance of the THS4001, it is essential that proper printed-circuit board high frequency design techniques be followed. A general set of guidelines is given below. In addition, a THS4001 evaluation board is available to use as a guide for layout or for evaluating the device performance.

- Ground planes It is highly recommended that a ground plane be used on the board to provide all
 components with a low inductive ground connection. However, in the areas of the amplifier inputs and
 output, the ground plane can be removed to minimize the stray capacitance.
- Proper power supply decoupling Use a 6.8-μF tantalum capacitor in parallel with a 0.1-μF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-μF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-μF capacitor should be placed as close as possible to the supply terminal. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- Sockets Sockets are not recommended for high speed op amps. The additional lead inductance in the socket pins will often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board is the best implementation.
- Short trace runs/compact part placements Optimum high frequency performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This will help to minimize stray capacitance at the input of the amplifier.



circuit layout considerations (continued)

Surface-mount passive components – Using surface mount passive components is recommended for high
frequency amplifier circuits for several reasons. First, because of the extremely low lead inductance of
surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small
size of surface-mount components naturally leads to a more compact layout thereby minimizing both stray
inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be
kept as short as possible.

evaluation board

An evaluation board is available for the THS4001 (literature number SLOP119). This board has been configured for very low parasitic capacitance in order to realize the full performance of the amplifier. A schematic of the evaluation board is shown in Figure 23. The circuitry has been designed so that the amplifier may be used in either an inverting or noninverting configuration. To order the evaluation board contact your local TI sales office or distributor. For more detailed information, refer to the *THS4001 EVM User's Manual* (literature number SLOU017).

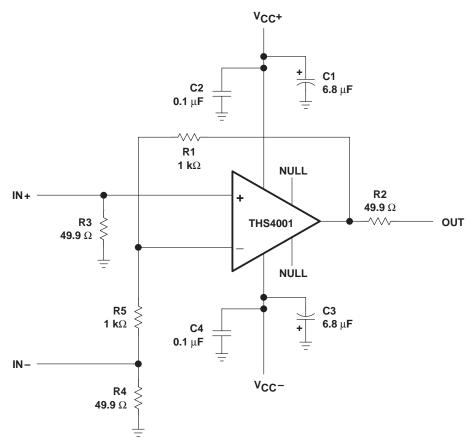


Figure 23.

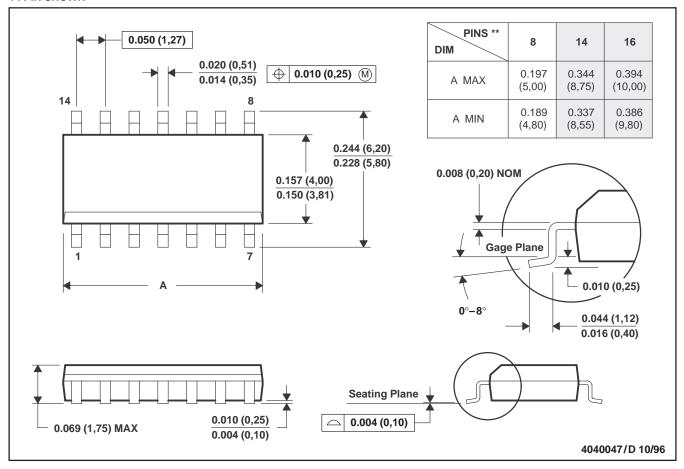


MECHANICAL INFORMATION

D (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-012

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